

650 V Power SiC Gen 3 Merged PIN Schottky Diode, 10 A



LINKS TO ADDITIONAL RESOURCES

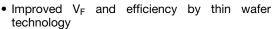




PRIMARY CHARACTERISTICS				
I _{F(AV)}	10 A			
V_R	650 V			
V _F at I _F at 150 °C	1.46 V			
T _J max.	175 °C			
I _R at V _R at 175 °C	4.5 μA			
Q _C (V _R = 400 V)	29 nC			
Package	TO-220AC 2L			
Circuit configuration	Single			

FEATURES

 Majority carrier diode using Schottky technology on SiC wide band gap material





- Positive V_F temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 2 whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		650	V	
Average rectified forward current	I _{F(AV)}	T _C = 130 °C (DC)	10	Α	
DC blocking voltage	V_{DC}		650	٧	
Repetitive peak forward current	I _{FRM}	T_C = 25 °C, f = 50 Hz, square wave, DC = 25 %	41	Α	
Non-repetitive peak forward surge current	I _{FSM}	$T_C = 25$ °C, $t_p = 10$ ms, half sine wave	60	А	
		$T_C = 110 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, half sine wave	58		
Power dissipation	P _{tot} (1)	T _C = 25 °C	64	W	
		T _C = 110 °C	28		
l ² t value	∫i ² dt	$T_C = 25 ^{\circ}C$	18	- A ² s	
		T _C = 110 °C	17		
Operating junction and storage temperatures	T _J ⁽²⁾ , T _{Stg}		-55 to +175	°C	

Notes

⁽¹⁾ Based on maximum R_{th}

 $^{^{(2)}}$ The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta JA}$



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Forward voltage V _F	I _F = 10 A	-	1.3	1.5		
	V_{F}	I _F = 10 A, T _J = 150 °C	-	1.46	1.85	V
		I _F = 10 A, T _J = 175 °C	-	1.52	-	
Reverse leakage current I _R		$V_R = V_R$ rated	-	0.7	55	
	I _R	V _R = V _R rated, T _J = 150 °C	-	2.8	125	μA
	V _R = V _R rated, T _J = 175 °C	-	4.5	-		
Total capacitance C	(V _R = 1 V, f = 1 MHz	-	445	=.	nE
		V _R = 400 V, f = 1 MHz	-	43	-	pF
Total capacitive charge	$Q_{\mathbb{C}}$	V _R = 400 V, f = 1 MHz	-	29	-	nC

THERMAL - MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-case	R _{thJC}		-	1.8	2.3	°C/W
Marking device				3C10l	ET07T	

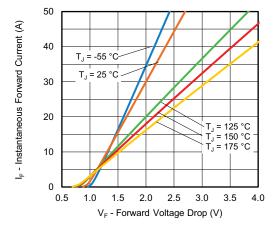


Fig. 1 - Typical Forward Voltage Drop Characteristics

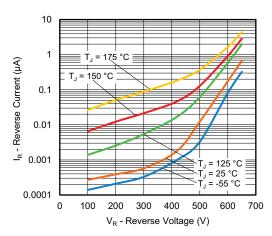


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

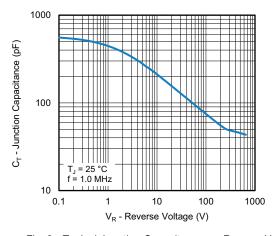


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

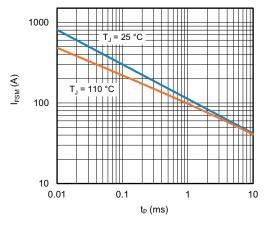


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)



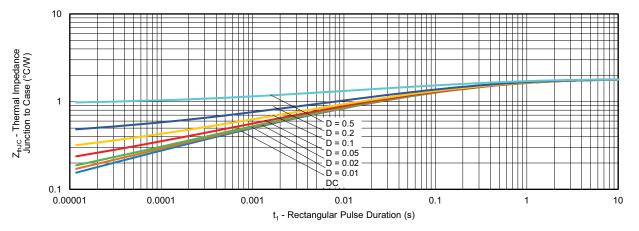


Fig. 5 - Typical Thermal Impedance Z_{thJC} Characteristics

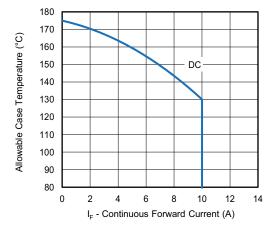


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

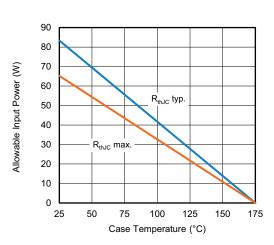


Fig. 7 - Forward Power Loss Characteristics

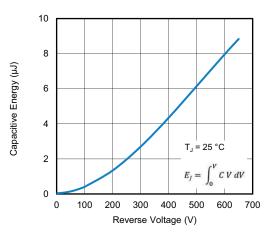


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

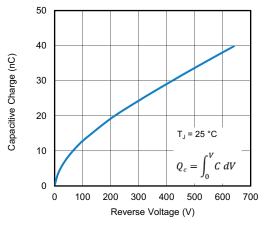
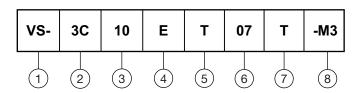


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

- 3C = SiC diode, Generation 3

Current rating (10 = 10 A)

- E = single diode

5 - Package TO-220

6 - Voltage rating: (07 = 650 V)

7 - T = true 2 pin

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION				
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION		
VS-3C10ET07T-M3	50/tube	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?96069		
Part marking information	www.vishay.com/doc?95391		



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